STARPOWER

SEMICONDUCTOR

MOSFET

MD900FFM100B7S

100V/900A 6 in one-package

General Description

STARPOWER MOSFET Power Module provides very low $R_{DS(on)}$ as well as optimized intrinsic diode. It's designed for the applications such SMPS and DC drives.

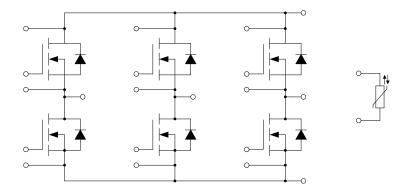
Features

- Low R_{DS(on)}
- Optimized intrinsic reverse diode
- Low inductance case avoid oscillations
- Kelvin source terminals for easy drive
- Isolated heatsink using DBC technology

Typical Applications

- Main and auxiliary AC drives of electric vehicles
- DC servo and robot drives
- Battery vehicles
- UPS equipment
- Plasma cutting

Equivalent Circuit Schematic



Absolute Maximum Ratings

MOSFET

Symbol	Description	Value	Unit
$ m V_{DSS}$	Drain-Source Voltage	100	V
$ m V_{GSS}$	Gate-Source Voltage	±30	V
I_{D}	Drain Current	900	A
$\overline{I_{DM}}$	Pulsed Drain Current	2680	A

Inverse Diode

Symbol	Description	Value	Unit
I_S	Source Current	900	Α
I_{SM}	Pulsed Source Current	2680	Α

Module

Symbol	Description Value		Unit
T _{imax}	Maximum Junction Temperature	175	°C
T_{jop}	Operating Junction Temperature	-40 to +150	°C
T_{STG}	Storage Temperature Range	-40 to +125	°C
$V_{\rm ISO}$	Isolation Voltage RMS,f=50Hz,t=1min	2500	V
M	Terminal Connection Torque, Screw M5	2.5 to 5.0	N.m

MOSFET Characteristics

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
R _{DS(on)}	Static Drain-Source On-Resistance	I_D =400A, V_{GS} =10V, T_j =25°C			2.25	mΩ
$V_{\text{GS(th)}}$	Gate-Source Threshold Voltage	$I_D=1.0 \text{mA}, V_{DS}=V_{GS}, T_j=25^{\circ}\text{C}$	3.0		5.0	V
$g_{ m fs}$	Forward Transconductance	$V_{DS} = 50V, I_D = 400A$	208			S
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=V_{DSS}, V_{GS}=0V,$ $T_i=25^{\circ}C$			100	μΑ
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=V_{GSS}, V_{DS}=0V,$ $T_i=25^{\circ}C$			400	nA
R_{Gint}	Internal Gate Resistance			0.68		Ω
C_{iss}	Input Capacitance			27.2		nF
C_{oss}	Output Capacitance	V_{GS} =0V, V_{DS} =25V, f=1.0MHz		9.88		nF
C_{rss}	Reverse Transfer Capacitance			3.96		nF
Q_g	Total Gate Charge			1040		nC
Q_{gs}	Gate-Source Charge	I_D =400A, V_{DS} =80V, V_{GS} =10V		196		nC
Q_{gd}	Gate-Drain ("Miller") Charge			640		nC
$t_{d(on)}$	Turn-On Delay Time	$ \begin{array}{c} V_{DS} = 50 \text{V}, I_D = 400 \text{A}, \\ R_G = 0.26 \Omega, V_{GS} = 10 \text{V}, \\ T_j = 25 ^{\circ} \text{C} \end{array} $		25		ns
$t_{\rm r}$	Rise Time			270		ns
$t_{d(off)}$	Turn-Off Delay Time			45		ns
$t_{\rm f}$	Fall Time			140		ns

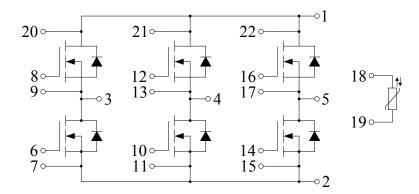
Inverse Diode Characteristics

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
V_{SD}	Diode Forward Voltage	I_S =400A, V_{GS} =0V, T_j =25°C			1.30	V
t_{rr}	Diode Reverse Recovery Time	V_R =50V, I_S =400A, -di/dt=400A/ μ s, T_j =25°C, V_{GS} =0V			220	ns
Qr	Diode Reverse Recovery Charge			6.56		μС

NTC Characteristics

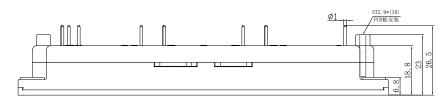
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
R ₂₅	Rated Resistance	$T_j=25^{\circ}C$		5.0		kΩ
$\Delta R/R$	Deviation of R ₁₀₀	$T_j=100^{\circ}\text{C}, R_{100}=493.3\Omega$	-5		5	%
P ₂₅	Power Dissipation				20.0	mW
B _{25/50}	B-value	R ₂ =R ₂₅ exp[B _{25/50} (1/T ₂ - 1/(298.15K))]		3375		K

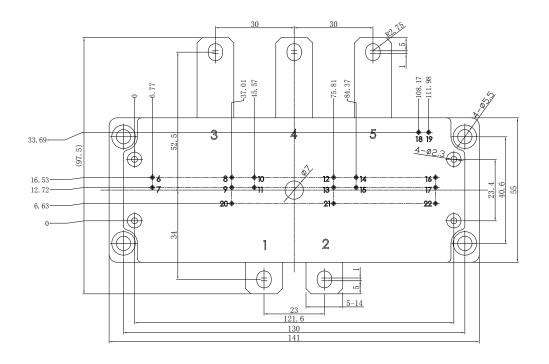
Circuit Schematic

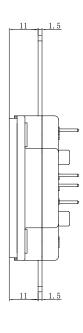


Package Dimensions

Dimensions in Millimeters







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